NSN 5962-01-349-2196

Memory Microcircuit - Page 1 of 1



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Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and programmable and radiation hardened

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

14 input

Criticality Code Justification:

Feat

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

And gate array

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

40.00 nanoseconds propagation delay

Memory Device Type:

Pal

Special Features:

Nuclear hardness critical item

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0